# Supplementary information

## Wide Channel Broadband $CH_3NH_3PbI_3$/SnS Hybrid Photodetector: Breaking the Limit of Bandgap Energy Operation

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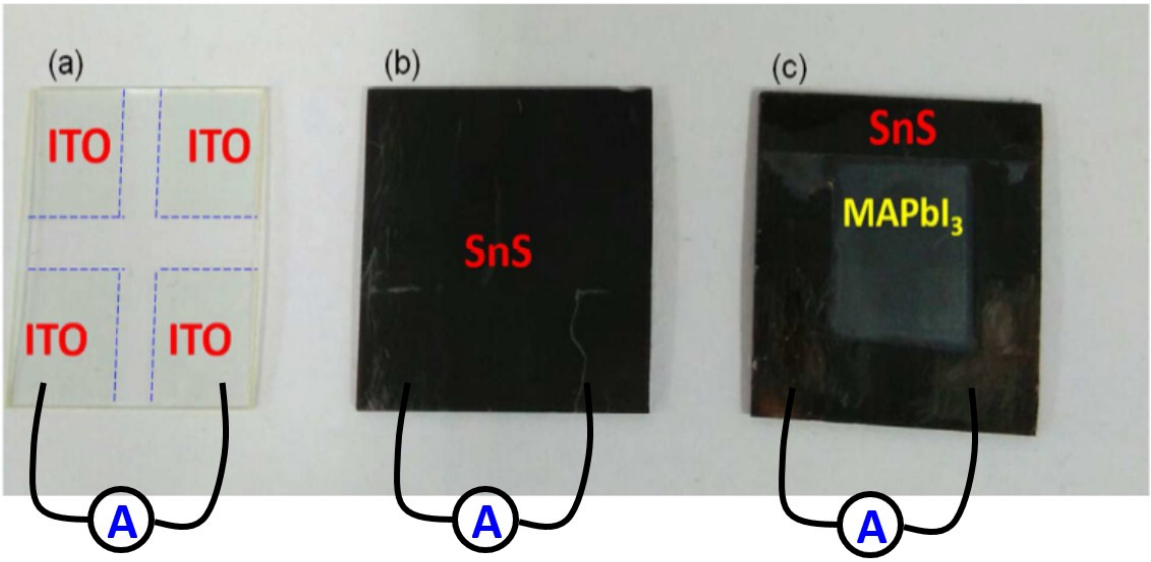


**Figure S1**. A photograph of the device. (a) The cross-shape patterned ITO, (b) SnS on patterned ITO, (c) Perovskite on top of the device.

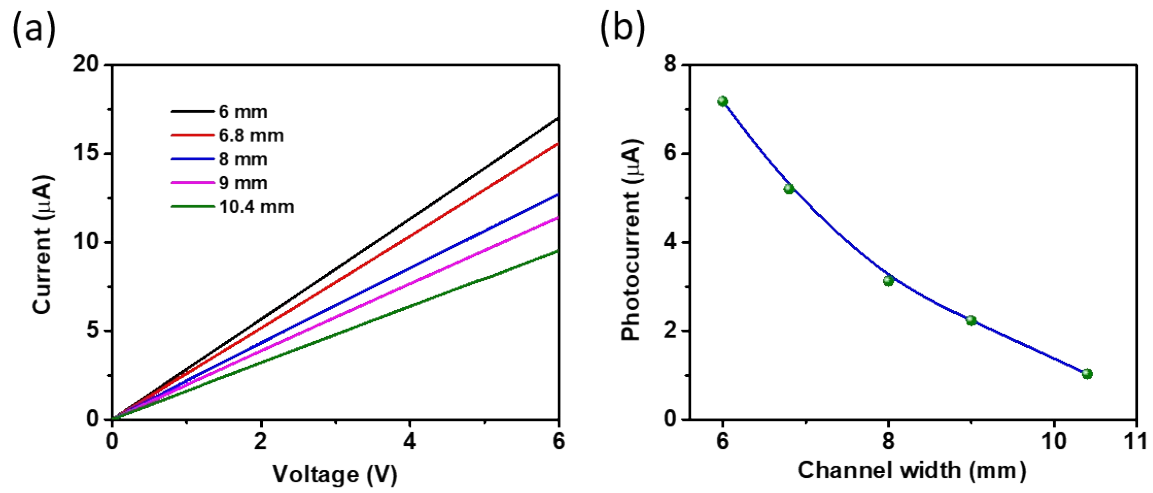


**Figure S2**. a) Dark *I-V* characteristics of the $CH_3NH_3PbI_3$/SnS device width different channel widths, b) The change in the photocurrent as a function of channel width.